

January 1989

Features

- This Circuit Is Processed in Accordance to Mil-Std-883 and is Fully Conformant Under the Provisions of Paragraph 1.2.1.
- Low Supply Current (Both Amplifiers) 500 μ A (Max)
- Wide Supply Voltage Range..... Single 3V to 30V or Dual ± 1.5 to ± 15 V
- High Slew Rate +S.R. 4V/ μ s (Min)
6V/ μ s (Typ)
- Low V_{OS} Drift (Over Full Temp) 3 μ V/ $^{\circ}$ C (Typ)
- Low Noise (1kHz)..... 15nV/ $\sqrt{\text{Hz}}$ (Typ)
- 100% Tested at ± 15 V and +5V Power Supplies
- Dielectric Isolation

Applications

- Portable Instruments
- Meter Amplifiers
- Telephone Headsets
- Microphone Amplifiers
- Remote Sensor/Transmitter
- Battery Powered Equipment
- For Further Design Ideas See App. Note 544

Description

The HA-5152/883 dual operational amplifier is part of a family of dielectrically isolated bipolar amplifiers designed to provide excellent AC performance while drawing less than 250 μ A of supply current per amplifier at +25 $^{\circ}$ C. This series consists of single (5151), dual (5152) or quad (5154), unity gain stable amplifiers which are especially well suited for portable and lightweight equipment where available power is limited.

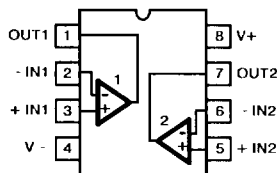
The HA-5152/883 combines superior low power AC performance with DC precision not usually found in general purpose amplifiers. The DC performance is centered around low input offset voltage (3mV), low offset voltage drift (3 μ V/ $^{\circ}$ C), and low input bias current (250nA). This is combined with a very low input noise voltage of 15nV/ $\sqrt{\text{Hz}}$ at 1kHz.

The AC performance of the HA-5152/883 surpasses that of typical low power amplifiers with 4V/ μ s slew rate and a full power bandwidth of 64kHz. This makes the HA-5152/883 an excellent choice for virtually all audio processing applications as well as remote sensor/transmitter designs requiring both low power and high speed. The suitability of the HA-5152/883 for remote and low power operation is further enhanced by the wide range of supply voltages (± 1.5 V to ± 15 V) as well as single supply operation (3V to 30V).

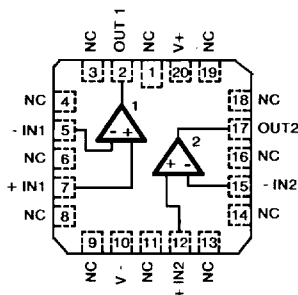
The HA-5152/883 is available in 8 pin Ceramic Mini-DIP, 20 pad Ceramic LCC or 8 pin (TO-99) Metal Can, and is interchangeable with most other operational amplifiers in their class.

Pinouts

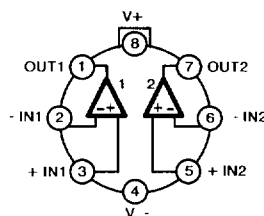
HA7-5152/883 (CERAMIC MINI-DIP)
TOP VIEW



HA4-5152/883 (CERAMIC LCC)
TOP VIEW



HA2-5152/883 (METAL CAN)
TOP VIEW



Specifications HA-5152/883

Absolute Maximum Ratings

Voltage Between V+ and V- Terminals	35V
Differential Input Voltage	7V
Voltage at Either Input Terminal	V+ to V-
Output Current	Full Short Circuit Protection
Output Current Duration	Indefinite, One Amplifier Shorted to Ground
Junction Temperature (T _J)	+175°C
Storage Temperature Range	-65°C to +150°C
ESD Rating	<2000V
Lead Temperature (Soldering 10 sec)	+275°C

CAUTION: Absolute maximum ratings are limiting values, applied individually beyond which the serviceability of the circuit may be impaired. Functional operability under any of these conditions is not necessarily implied.

Thermal Information

	θ_{ja}	θ_{jc}
Ceramic DIP Package	82°C/W	26°C/W
Ceramic LCC Package	74°C/W	20°C/W
Metal Can Package	111°C/W	35°C/W
Package Power Dissipation Limit at +75°C For T _J ≤ +175°C		
Ceramic DIP Package	1.22W	
Ceramic LCC Package	1.35W	
Metal Can Package	900mW	
Package Power Dissipation Derating Factor Above +75°C		
Ceramic DIP Package	12.2mW/°C	
Ceramic LCC Package	13.5mW/°C	
Metal Can Package	9mW/°C	

Recommended Operating Conditions

Operating Temperature Range	-55°C to +125°C	V _{INcm} ≤ 1/2 (V+ - V-)
Operating Supply Voltage	±1.5V to ±15V or 3V to 30V	R _L ≥ 10kΩ

TABLE 1. D.C. ELECTRICAL PERFORMANCE CHARACTERISTICS

Device Tested at: R_{SOURCE} = 100Ω, R_{LOAD} = 500kΩ, V_{OUT} = 0V, Unless Otherwise Specified.

Subscript 1 Refers to Supply Voltages (±V_S) = ±15V, Subscript 2 Refers to +V_S = 5.0V, -V_S = 0.0V.

D.C. PARAMETERS	SYMBOL	CONDITIONS	GROUP A SUBGROUP	TEMPERATURE	LIMITS		UNITS
					MIN	MAX	
Input Offset Voltage	V _{IO1}	V _{CM} = 0V	1	+25°C	-3	3	mV
			2, 3	+125°C, -55°C	-4	4	mV
	V _{IO2}	V _{CM} = 0V V _{OUT} = 1.4V	1	+25°C	-3	3	mV
			2, 3	+125°C, -55°C	-4	4	mV
Input Bias Current	+I _{B1}	V _{CM} = 0V +R _S = 10kΩ -R _S = 100Ω	1	+25°C	-250	250	nA
			2, 3	+125°C, -55°C	-400	400	nA
	-I _{B1}	V _{CM} = 0V +R _S = 100Ω -R _S = 10kΩ	1	+25°C	-250	250	nA
			2, 3	+125°C, -55°C	-400	400	nA
	+I _{B2}	V _{CM} = 0V, V _{OUT} = 1.4V +R _S = 10kΩ -R _S = 100Ω	1	+25°C	-250	250	nA
			2, 3	+125°C, -55°C	-400	400	nA
	-I _{B2}	V _{CM} = 0V, V _{OUT} = 1.4V +R _S = 100Ω -R _S = 10kΩ	1	+25°C	-250	250	nA
			2, 3	+125°C, -55°C	-400	400	nA
Input Offset Current	I _{IO1}	V _{CM} = 0V +R _S = 10kΩ -R _S = 10kΩ	1	+25°C	-50	50	nA
			2, 3	+125°C, -55°C	-80	80	nA
	I _{IO2}	V _{CM} = 0V, V _{OUT} = 1.4V +R _S = 10kΩ -R _S = 10kΩ	1	+25°C	-50	50	nA
			2, 3	+125°C, -55°C	-80	80	nA
Common Mode Range	+CMR ₁	V+ = 5V V- = -25V	1	+25°C	10	-	V
			2, 3	+125°C, -55°C	10	-	V
	-CMR ₁	V+ = 25V V- = -5V	1	+25°C	-	-10	V
			2, 3	+125°C, -55°C	-	-10	V
	+CMR ₂	V+ = 5V to 2V V- = 0V to -3V V _{OUT} = 1.4V to -1.6V	1	+25°C	0 to 3	-	V
			2, 3	+125°C, -55°C	0 to 3	-	V

CAUTION: This device is sensitive to electrostatic discharge. Proper I.C. handling procedures should be followed.

TABLE 1. D.C. ELECTRICAL PERFORMANCE CHARACTERISTICS (Continued)

Device Tested at: $R_{SOURCE} = 100\Omega$, $R_{LOAD} = 500k\Omega$, $V_{OUT} = 0V$, Unless Otherwise Specified.

Subscript 1 Refers to Supply Voltages ($\pm V_S$) = $\pm 15V$; Subscript 2 Refers to $+V_S = 5.0V$, $-V_S = 0.0V$.

D.C. PARAMETERS	SYMBOL	CONDITIONS	GROUP A SUBGROUP	TEMPERATURE	LIMITS		UNITS
					MIN	MAX	
Large Signal Voltage Gain	+A _{VOL1}	$V_{OUT} = 0V$ and $10V$ $R_L = 10k\Omega$	4	+25°C	50	-	kV/V
			5, 6	+125°C, -55°C	25	-	kV/V
	-A _{VOL1}	$V_{OUT} = 0V$ and $-10V$ $R_L = 10k\Omega$	4	+25°C	50	-	kV/V
			5, 6	+125°C, -55°C	25	-	kV/V
	+A _{VOL2}	$V_{OUT} = 1.4V$ and $2.5V$ $R_L = 10k\Omega$	4	+25°C	50	-	kV/V
			5, 6	+125°C, -55°C	25	-	kV/V
Common Mode Rejection Ratio	+CMRR ₁	$\Delta V_{CM} = 10V$ $+V = 5V$ $-V = -25V$ $V_{OUT} = -10V$	1	+25°C	80	-	dB
			2, 3	+125°C, -55°C	80	-	dB
	-CMRR ₁	$\Delta V_{CM} = 10V$ $+V = 25V$ $-V = -5V$ $V_{OUT} = 10V$	1	+25°C	80	-	dB
			2, 3	+125°C, -55°C	80	-	dB
	+CMRR ₂	$\Delta V_{CM} = 0V$ to $3V$ $+V = 2V$ $-V = -3V$ $V_{OUT} = -3V$	1	+25°C	80	-	dB
			2, 3	+125°C, -55°C	80	-	dB
Output Voltage Swing	+V _{OUT1}	$R_L = 10k\Omega$	1	+25°C	10	-	V
			2, 3	+125°C, -55°C	10	-	V
	-V _{OUT1}	$R_L = 10k\Omega$	1	+25°C	-	-10	V
			2, 3	+125°C, -55°C	-	-10	V
	+V _{OUT2}	$R_L = 10k\Omega$ Terminated at 2.5V	1	+25°C	3.2	-	V
			2, 3	+125°C, -55°C	2.9	-	V
Quiescent Power Supply Current (Both Amplifiers)	+I _{CC1}	$V_{OUT} = 0V$ $I_{OUT} = 0mA$	1	+25°C	-	500	μA
			2, 3	+125°C, -55°C	-	650	μA
	-I _{CC1}	$V_{OUT} = 0V$ $I_{OUT} = 0mA$	1	+25°C	-500	-	μA
			2, 3	+125°C, -55°C	-650	-	μA
	+I _{CC2}	$V_{OUT} = 1.4V$ $I_{OUT} = 0mA$	1	+25°C	-	500	μA
			2, 3	+125°C, -55°C	-	650	μA
Power Supply Rejection Ratio	+PSRR ₁	$\Delta V_{SUP} = 10V$ $+V = 10V, -V = -15V$ $+V = 20V, -V = -15V$	1	+25°C	80	-	dB
			2, 3	+125°C, -55°C	80	-	dB
	-PSRR ₁	$\Delta V_{SUP} = 10V$ $+V = 15V, -V = -10V$ $+V = 15V, -V = -20V$	1	+25°C	80	-	dB
			2, 3	+125°C, -55°C	80	-	dB
	+PSRR ₂	$\Delta V_{SUP} = 10V$ $+V = 5V, -V = 0V$ $+V = 15V, -V = 0V$	1	+25°C	80	-	dB
			2, 3	+125°C, -55°C	80	-	dB
Channel Separation	±CS	$R_L = 10k\Omega$	1	+25°C	80	-	dB
			2, 3	+125°C, -55°C	80	-	dB

TABLE 2. A.C. ELECTRICAL PERFORMANCE CHARACTERISTICS

Device Tested at: $R_{SOURCE} = 50\Omega$, $R_{LOAD} = 10k\Omega$, $C_{LOAD} = 100pF$, $V_{OUT} = 0V$, Unless Otherwise Specified.Subscript 1 Refers to Supply Voltages ($\pm V_S$) = $\pm 15V$; Subscript 2 Refers to $+V_S = 5.0V$, $-V_S = 0.0V$.

PARAMETERS	SYMBOL	CONDITIONS	GROUP A SUBGROUP	TEMPERATURE	LIMITS		UNITS
					MIN	MAX	
Slew Rate	+SR ₁	$V_{OUT} = -3V$ to $3V$ V_{IN} S.R. $\leq 25V/\mu s$	4	+25°C	4	-	V/ μs
	-SR ₁	$V_{OUT} = 3V$ to $-3V$ V_{IN} S.R. $\leq 25V/\mu s$	4	+25°C	4	-	V/ μs
	+SR ₂	$V_{OUT} = 0V$ to $3V$ V_{IN} S.R. $\leq 25V/\mu s$	4	+25°C	2	-	V/ μs
	-SR ₂	$V_{OUT} = 3V$ to $0V$ V_{IN} S.R. $\leq 25V/\mu s$	4	+25°C	2	-	V/ μs

TABLE 3. ELECTRICAL PERFORMANCE CHARACTERISTICS

Device Tested at: $R_{SOURCE} = 50\Omega$, $R_{LOAD} = 10k\Omega$, $C_{LOAD} = 100pF$, $A_V = 1V/V$, Unless Otherwise Specified.Subscript 1 Refers to Supply Voltages ($\pm V_S$) = $\pm 15V$; Subscript 2 Refers to $+V_S = 5.0V$, $-V_S = 0.0V$.

PARAMETERS	SYMBOL	CONDITIONS	NOTES	TEMPERATURE	LIMITS		UNITS
					MIN	MAX	
Gain Bandwidth Product	GBWP	$V_O = 200mV$, $f_O = 10kHz$	1	+25°C	0.7	-	MHz
Full Power Bandwidth	FPBW ₁	$V_{PEAK} = 10V$	1, 2	+25°C	64	-	kHz
	FPBW ₂	$V_{PEAK} = 1.1V$ $V_{Ref} = 2.5V$	1, 2	+25°C	290	-	kHz
Minimum Closed Loop Stable Gain	CLSG	$R_L = 10k\Omega$, $C_L = 100pF$	1	-55°C to +125°C	1	-	V/V
Quiescent Power Consumption	PC ₁	$V_{OUT} = 0V$, $I_{OUT} = 0mA$	1, 3	-55°C to +125°C	-	16.5	mW
	PC ₂	$V_{OUT} = 1.4V$, $I_{OUT} = 0mA$	1, 3	-55°C to +125°C	-	2.75	mW

NOTES: 1. Parameters listed in Table 3 are controlled via design or process parameters and are not directly tested at final production. These parameters are lab characterized upon initial design release, or upon design changes. These parameters are guaranteed by characterization based upon data from multiple production runs which reflect lot to lot and within lot variation.

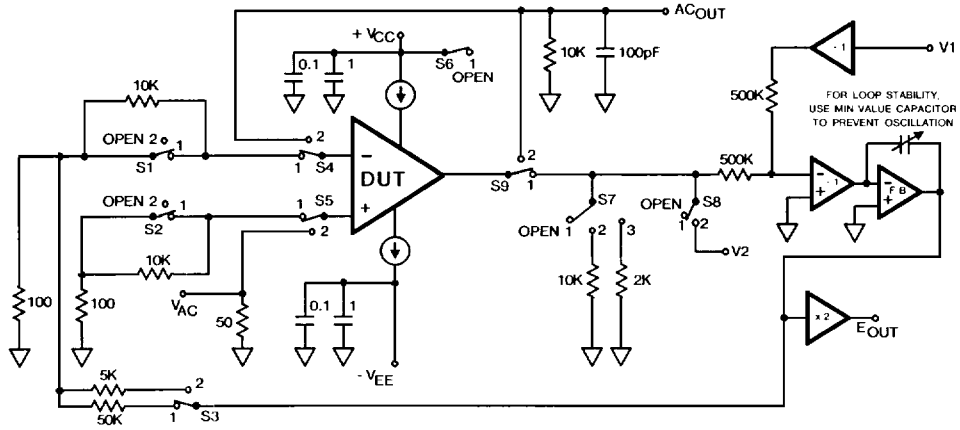
2. Full Power Bandwidth guarantee based on Slew Rate measurement using $FPBW = \text{Slew Rate} / (2\pi V_{PEAK})$.

3. Quiescent Power Consumption based upon Quiescent Supply Current test maximum. (No load on outputs.)

TABLE 4. ELECTRICAL TEST REQUIREMENTS

MIL-STD-883 TEST REQUIREMENTS	SUBGROUPS (SEE TABLES 1 & 2)
Interim Electrical Parameters (Pre Burn-in)	1
Final Electrical Test Parameters	1*, 2, 3, 4, 5, 6
Group A Test Requirements	1, 2, 3, 4, 5, 6
Groups C & D Endpoints	1

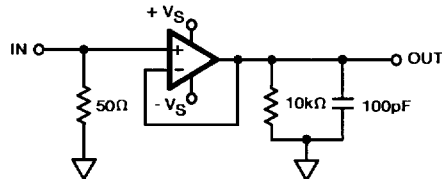
* PDA applies to Subgroup 1 only.

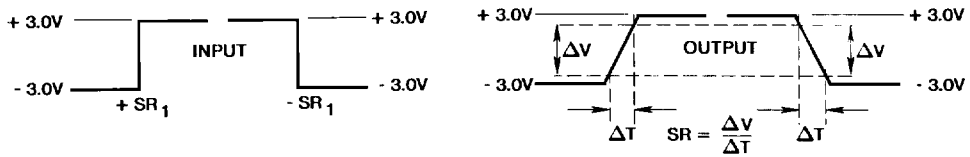
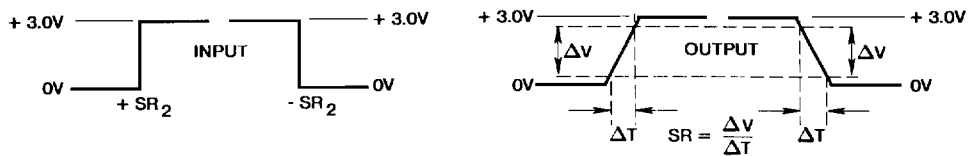
Test Circuit (Applies to Tables 1 and 2)


ONE OF TWO TEST LOOPS FOR THE HA - 5152/883

ALL RESISTORS = $\pm 1\%$ (Ω)
ALL CAPACITORS = $\pm 10\%$ (μF)

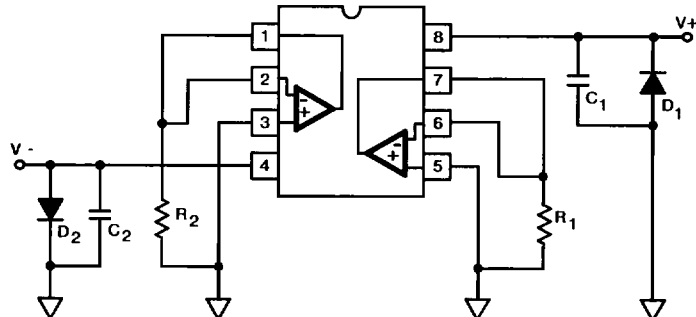
For Detailed Information, Refer to HA-5152/883 Test Tech Brief

Test Waveforms
SIMPLIFIED TEST CIRCUIT (Applies to Table 2)

NOTE: $\pm V_{SUPPLY}$ ($\pm V_S$) Tested with $\pm 15V$ and $0V$, $+5V$. V_{IN} Slew Rate Maintained with Less Than $10V/\mu s$ Input for Voltage Follower Configuration.

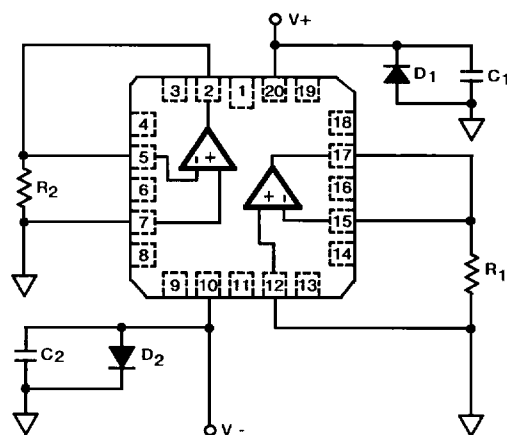
SLEW RATE WAVEFORMS, $A_V = 1V/V$
 $\pm V_{SUPPLY} = \pm 15V$

 $+V_{SUPPLY} = 5V$, $-V_{SUPPLY} = 0V$


Burn-In Circuits

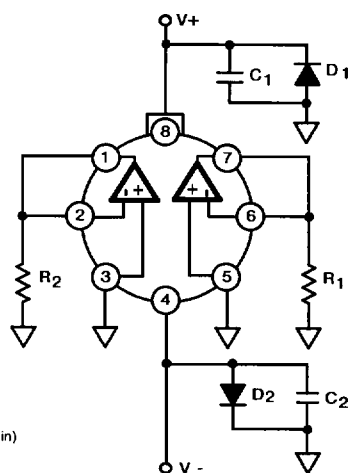
HA7-5152/883 CERAMIC DIP



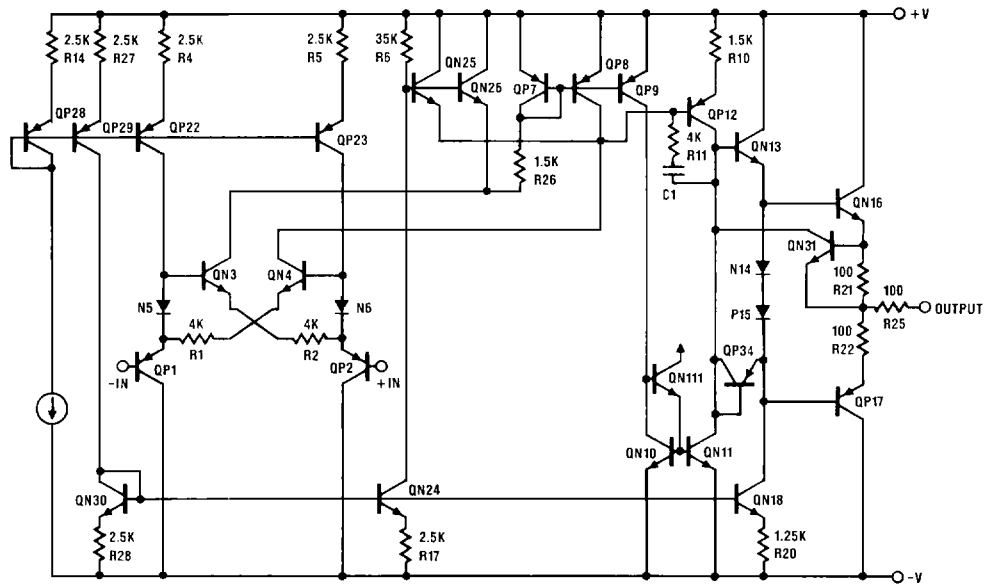
HA4-5152/883 CERAMIC LCC



HA2-5152/883 TO-99 METAL CAN

**NOTES:** $R_1 = R_2 = 2k\Omega, \pm 5\%, 1/4W$ (Min) $C_1 = C_2 = 0.01\mu F/\text{Socket}$ (Min) or $0.1\mu F/\text{Row}$, (Min) $D_1 = D_2 = \text{IN4002 or Equivalent/Board}$ $|V(+)-V(-)| = 30V$

Schematic Diagram (1/2 Of HA-5152/883)



ALL RESISTORS = (Ω)

Die Characteristics**DIE DIMENSIONS:**

53.9 x 103.1 x 19 mils
(1370 x 2620 x 483 μm)

METALLIZATION:

Type: Aluminum
Thickness: $16\text{k}\text{\AA} \pm 2\text{k}\text{\AA}$

WORST CASE CURRENT DENSITY:

$0.6 \times 10^5 \text{A/cm}^2$ @ 2.5mA

SUBSTRATE POTENTIAL (Powered Up): V-

GLASSIVATION:

Type: Nitride
Thickness: $7\text{k}\text{\AA} \pm 0.7\text{k}\text{\AA}$

TRANSISTOR COUNT: 72

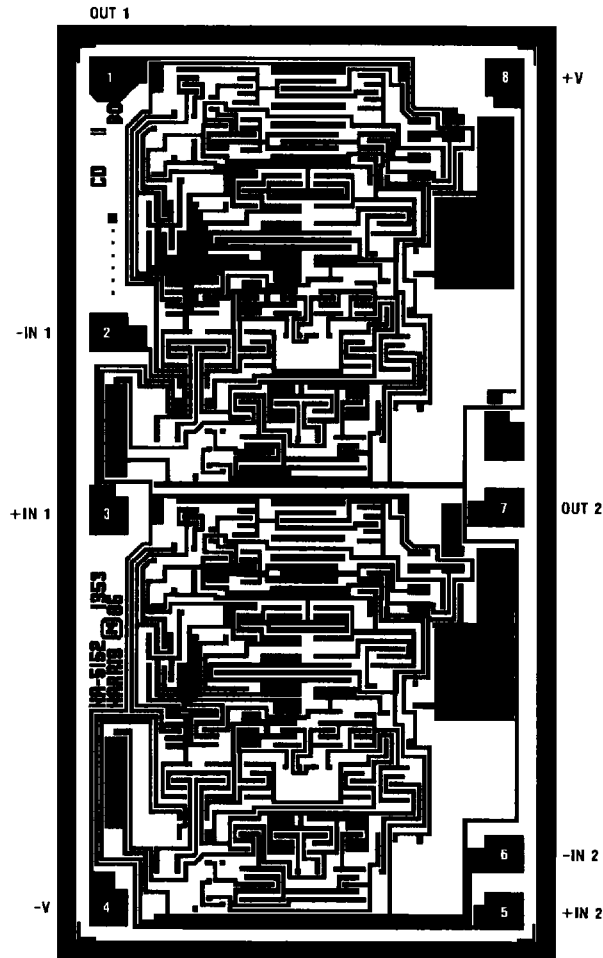
PROCESS: HFSB Bipolar/JFET Dielectric Isolation

DIE ATTACH:

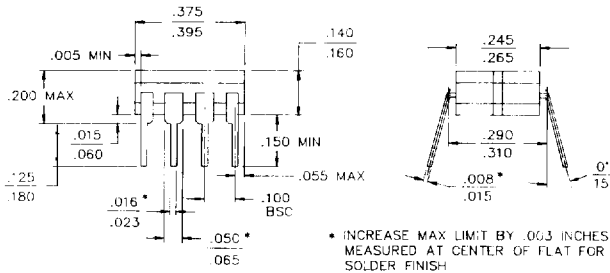
Material: Gold/Silicon Eutectic Alloy
Temperature: Ceramic DIP — 460°C (Max)
Ceramic LCC — 420°C (Max)
Metal Can — 420°C (Max)

Metallization Mask Layout

HA-5152/883



NOTE: Pad Numbers Refer to 8 Pin Ceramic Mini-DIP or Metal Can Package Pinouts Only.

Packaging †**8 PIN CERAMIC DIP****LEAD MATERIAL:** Type B**LEAD FINISH:** Type A**PACKAGE MATERIAL:** Ceramic, 90% Alumina**PACKAGE SEAL:**

Material: Glass Frit

Temperature: 450°C ± 10°C

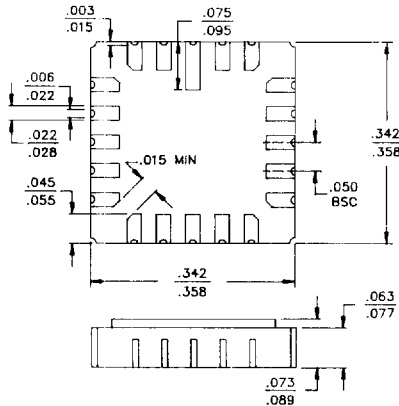
Method: Furnace Seal

INTERNAL LEAD WIRE:

Material: Aluminum

Diameter: 1.25 Mil

Bonding Method: Ultrasonic

COMPLIANT OUTLINE: 38510 D-4**20 PAD CERAMIC LCC****PAD MATERIAL:** Type C**PAD FINISH:** Type A**FINISH DIMENSION:** Type A**PACKAGE MATERIAL:** Ceramic, 90% Al₂O₃**PACKAGE SEAL:**

Material: Gold/Tin (80/20)

Temperature: 320°C ± 10°C

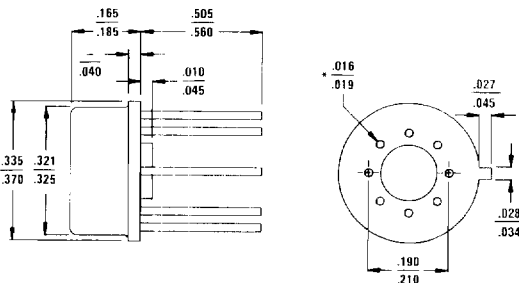
Method: Furnace Braze

INTERNAL LEAD WIRE:

Material: Aluminum

Diameter: 1.25 Mil

Bonding Method: Ultrasonic

COMPLIANT OUTLINE: 38510 C-2**8 PIN TO-99 METAL CAN****LEAD MATERIAL:** Type A**LEAD FINISH:** Type C**PACKAGE MATERIAL:** Kovar Header with Nickel Can**PACKAGE SEAL:**

Material: No Seal Material

Temperature: Room Temperature

Method: Resistance Weld

INTERNAL LEAD WIRE:

Material: Aluminum

Diameter: 1.25 Mil

Bonding Method: Ultrasonic Bonded

COMPLIANT OUTLINE: 38510 A-1

*Dimension Maximum Limits Are Increased by 0.003 inches for Solder Dip Finish

NOTE: All Dimensions are Min Max. Dimensions are in inches.

† Mil-M-38510 Compliant Materials, Finishes, and Dimensions.

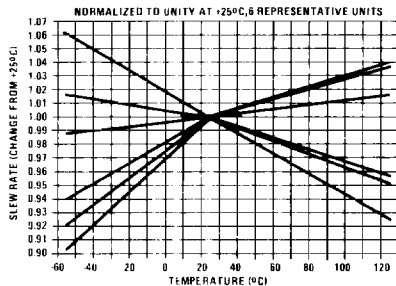
DESIGN INFORMATION

Dual, Low Power Operational Amplifier

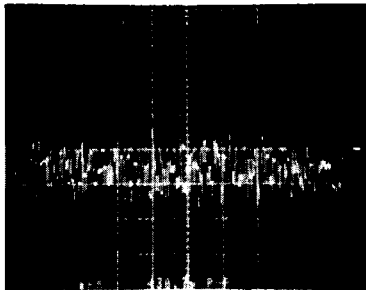
The information contained in this section has been developed through characterization by Harris Semiconductor and is for use as application and design aid only. These characteristics are not 100% tested and no product guarantee is implied.

Typical Performance Curves Unless Otherwise Specified: $T_A = +25^\circ\text{C}$, $V_{\text{SUPPLY}} = \pm 15\text{V}$

SLEW RATE vs. TEMPERATURE
Normalized to Unity at $+25^\circ\text{C}$, 6 Representative Units

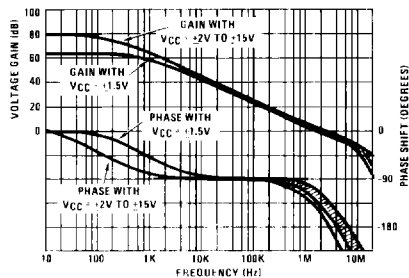


PEAK-TO-PEAK NOISE 0.1Hz TO 10Hz
 $T_A = +25^\circ\text{C}$, $A_V = 1000\text{V/V}$

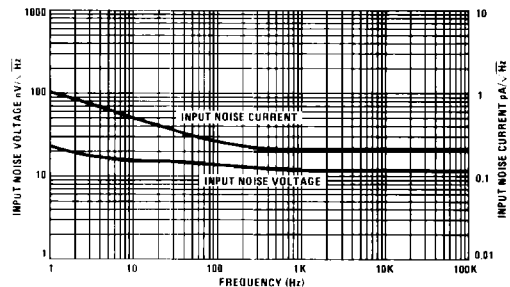


Vertical Scale: (Volts: 100µs/Div.)
Horizontal Scale: (Time: 1sec/Div.)
430nV_{p-p} RTI

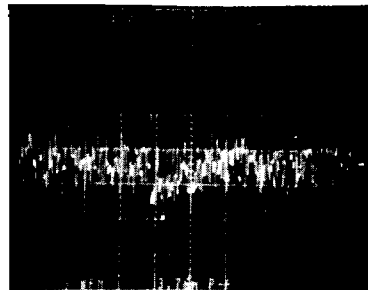
FREQUENCY RESPONSE vs. SUPPLY VOLTAGE
 $T_A = +25^\circ\text{C}$, $R_L = 10\text{K}$, $C_L = 100\text{pF}$



NOISE SPECTRAL DENSITY

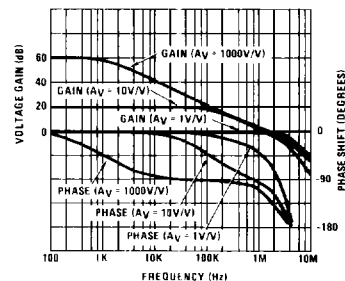


PEAK-TO-PEAK NOISE 0.1Hz TO 1MHz
 $T_A = +25^\circ\text{C}$, $A_V = 1000\text{V/V}$



Vertical Scale: (Volts: 1mV/Div.)
Horizontal Scale: (Time: 1sec/Div.)
3.70µV_{p-p} RTI

FREQUENCY RESPONSE AT VARIOUS GAINS
 $T_A = +25^\circ\text{C}$, $V_{\text{CC}} = \pm 15\text{V}$, $R_L = 10\text{K}$, $C_L = 100\text{pF}$

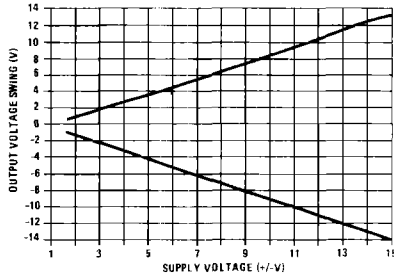


DESIGN INFORMATION (Continued)

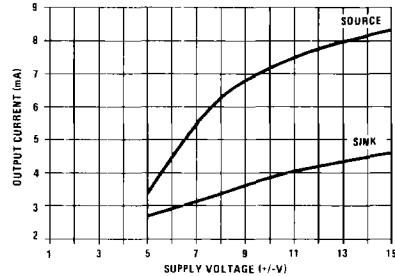
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Typical Performance Curves Unless Otherwise Specified: $T_A = +25^\circ\text{C}$, $V_{\text{SUPPLY}} = \pm 15\text{V}$

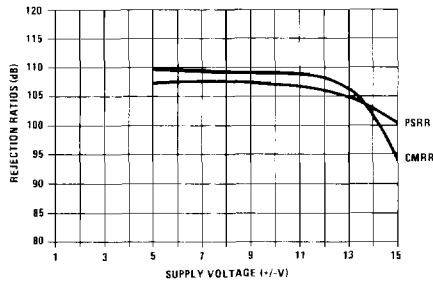
OUTPUT VOLTAGE SWING vs. SUPPLY VOLTAGE
($+25^\circ\text{C}$)



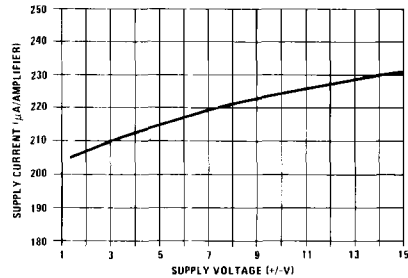
OUTPUT CURRENT vs. SUPPLY VOLTAGE
($+25^\circ\text{C}$)



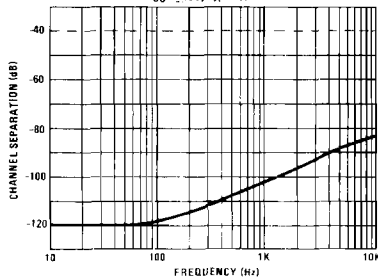
CMRR AND PSRR vs. SUPPLY VOLTAGE
($+25^\circ\text{C}$)



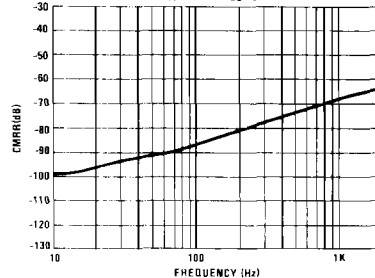
SUPPLY CURRENT vs. SUPPLY VOLTAGE
Per Amplifier ($+25^\circ\text{C}$)



CHANNEL SEPARATION vs. FREQUENCY
 $V_{CC} = \pm 15\text{V}$, $T_A = +25^\circ\text{C}$
 $V_{CC} = \pm 15\text{V}$, $T_A = +25^\circ\text{C}$



CMRR vs. FREQUENCY
 $T_A = +25^\circ\text{C}$, $V_{CC} = \pm 15\text{V}$
 $T_A = +25^\circ\text{C}$, $V_{CC} = \pm 15\text{V}$

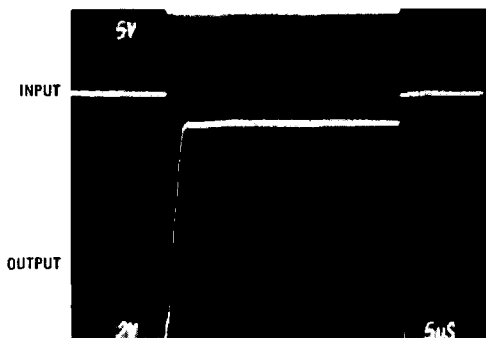


DESIGN INFORMATION (Continued)

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Typical Performance Curves Unless Otherwise Specified: $T_A = +25^\circ\text{C}$, $V_{\text{SUPPLY}} = \pm 15\text{V}$ **MEASURED LARGE SIGNAL RESPONSE**

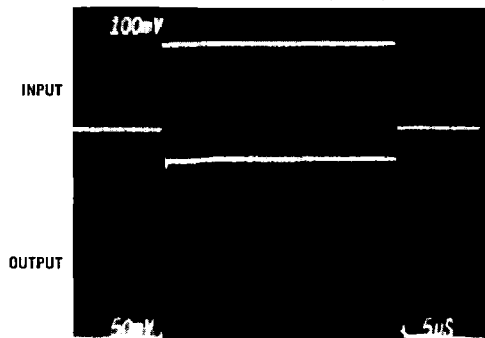
Vertical Scale: (Volts: Input = 5V/Div.; Output = 2V/Div.)
Horizontal Scale: (Time: 5 μs /Div.)



$+V_{\text{SUPPLY}} = +15\text{V}$, $-V_{\text{SUPPLY}} = -15\text{V}$

MEASURED SMALL SIGNAL RESPONSE

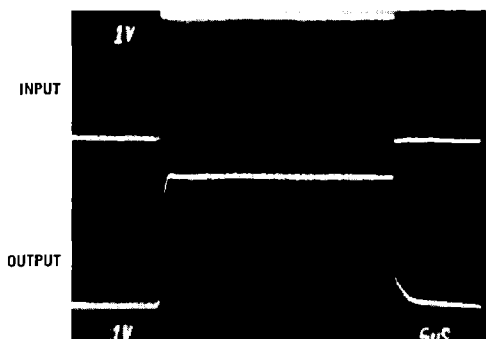
Vertical Scale: (Volts: Input = 100mV/Div.; Output = 50mV/Div.)
Horizontal Scale: (Time: 5 μs /Div.)



$+V_{\text{SUPPLY}} = +15\text{V}$, $-V_{\text{SUPPLY}} = -15\text{V}$

MEASURED LARGE SIGNAL RESPONSE

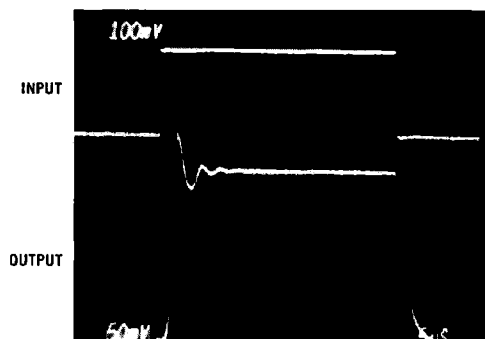
Vertical Scale: (Volts: Input = 1V/Div.; Output = 1V/Div.)
Horizontal Scale: (Time: 5 μs /Div.)



$+V_{\text{SUPPLY}} = +5\text{V}$, $-V_{\text{SUPPLY}} = 0\text{V}$

MEASURED SMALL SIGNAL RESPONSE

Vertical Scale: (Volts: Input = 100mV/Div.; Output = 50mV/Div.)
Horizontal Scale: (Time: 5 μs /Div.)



$+V_{\text{SUPPLY}} = +5\text{V}$, $-V_{\text{SUPPLY}} = 0\text{V}$

DESIGN INFORMATION (Continued)

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TYPICAL PERFORMANCE CHARACTERISTICS

Device Characterized at: Supply Voltage = 0V, 5 to ± 15 V, $R_L = 10k\Omega$, $C_L = 100pF$, Unless Otherwise Specified.

PARAMETERS	CONDITIONS	TEMP	TYPICAL	DESIGN LIMIT	UNITS
Offset Voltage	$V_{CM} = 0V$	Full	0.5	Table 1	mV
Offset Voltage Drift	Versus Temperature	Full	3	6	$\mu V/^\circ C$
Bias Current	$V_{CM} = 0V$	+25 $^\circ C$, +125 $^\circ C$	130	Table 1	nA
		-55 $^\circ C$	150	Table 1	nA
Offset Current	$V_{CM} = 0V$	Full	5	Table 1	nA
Differential Input Resistance		+25 $^\circ C$	1.5	1	M Ω
Input Noise Voltage	$f_o = 10Hz$	+25 $^\circ C$	18	25	$nV/\sqrt{Hz}$
	$f_o = 100Hz$	+25 $^\circ C$	15	20	$nV/\sqrt{Hz}$
	$f_o = 1kHz$	+25 $^\circ C$	14.8	18	$nV/\sqrt{Hz}$
Input Noise Current	$f_o = 10Hz$	+25 $^\circ C$	0.5	0.7	$pA/\sqrt{Hz}$
	$f_o = 100Hz$	+25 $^\circ C$	0.3	0.6	$pA/\sqrt{Hz}$
	$f_o = 1kHz$	+25 $^\circ C$	0.25	0.4	$pA/\sqrt{Hz}$
Large Signal Voltage Gain	$R_L = 10k\Omega$	+25 $^\circ C$, +125 $^\circ C$	150K	Table 1	V/V
		-55 $^\circ C$	100K	Table 1	V/V
CMRR		Full	105	Table 1	dB
PSRR		Full	105	Table 1	dB
Unity Gain Bandwidth	$f @ -3dB$	+25 $^\circ C$	1.3	0.7	MHz
+ Slew Rate	$V_S = 0V, 5V$	-55 $^\circ C$	4	2	V/ μs
	$V_S = 0V, 5V$ to $\pm 15V$	+25 $^\circ C$, +125 $^\circ C$	6.5	4	V/ μs
- Slew Rate	$V_S = 0V, 5V$	Full	12	2	V/ μs
	$V_S = \pm 15V$	Full	25	4	V/ μs
+ I_{OUT}		+25 $^\circ C$, +125 $^\circ C$	3	1.5	mA
		-55 $^\circ C$	0.8	0.4	mA
- I_{OUT}		-55 $^\circ C$, +25 $^\circ C$	-7.5	-6	mA
		+125 $^\circ C$	-4.5	-3.5	mA
Rise Time	$V_S = \pm 15V, V_O = 200mV$	Full	250	500	ns
Fall Time	$V_S = \pm 15V, V_O = -200mV$	-55 $^\circ C$, +25 $^\circ C$	110	300	ns
		+125 $^\circ C$	200	400	ns
Overshoot	$V_S = \pm 15V, V_O = \pm 200mV$	Full	2	10	%
Supply Current (All Four Amplifiers)	$V_S = 0V, 5V$	+25 $^\circ C$	350	Table 1	μA
	$V_S = \pm 15V$	+25 $^\circ C$	470	Table 1	μA